

Appl. No. 10/653,882  
Amendment dated: February 25, 2005  
Reply to OA of: February 1, 2005

This listing of claims will replace all prior versions and listings of claims in the application.

**Listing of Claims:**

1(original). A method for forming high aspect ratio contact holes, comprising steps of:

- providing a substrate;
- forming a pad oxide layer on said substrate;
- forming a pad nitride layer on said pad oxide layer;
- forming an oxide layer on said pad nitride layer;
- forming a mask of a predetermined pattern on said oxide layer; and
- forming contact holes by plasma etching, the plasma etching using a plasma composition comprising argon, oxygen, a first fluorocarbon and a second fluorocarbon, the fluorine-to-carbon ratio of said second fluorocarbon being higher than that of the first fluorocarbon.

2(original). The method as claimed in Claim 1, wherein said first fluorocarbon is  $C_5F_8$ .

3(original). The method as claimed in Claim 2, wherein the fluorine-to-carbon ratio of said second fluorocarbon is higher than 8:5.

4(original). The method as claimed in Claim 3, wherein said second fluorocarbon is  $C_3F_8$ .

5(original). A method for forming high aspect ratio contact holes, said method using plasma etching to open contact holes, and being characterized in that the plasma etching uses a plasma composition comprising argon, oxygen, a first fluorocarbon and

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a second fluorocarbon, the fluorine-to-carbon ratio of said second fluorocarbon being higher than that of the first fluorocarbon.

6(original). The method as claimed in Claim 5, wherein said first fluorocarbon is  $C_5F_8$ .

7(original). The method as claimed in Claim 6, wherein the fluorine-to-carbon ratio of said second fluorocarbon is higher than 8:5.

8(original). The method as claimed in Claim 7, wherein said second fluorocarbon is  $C_3F_8$ .

Claims 9-12(canceled).